ABSTRACT

The present invention relates to a hafnium silicide target for forming a gate oxide film composed of $HfSi_{1.02-2.00}$. Obtained is a hafnium silicide target superior in workability and embrittlement resistance, and suitable for forming a HfSiO film and HfSiON film that may be used as a high dielectric gate insulation film in substitute for a SiO_2 film, and to the manufacturing method thereof.



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